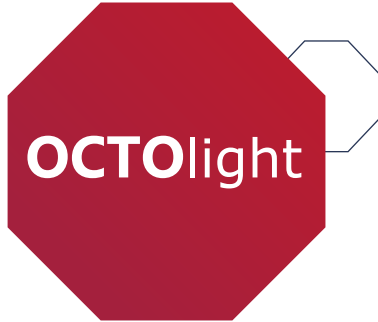




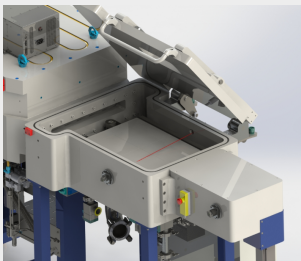
Single Module PECVD

"Your entry point to INDEOtec's PECVD World"



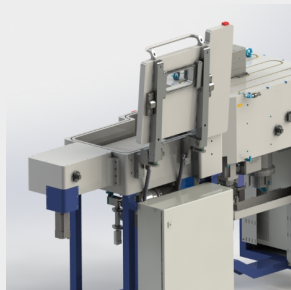
Compatible with all box-in-a-box PECVD modules made by INDEOtec

- > PECVD std
- > PECVD Mirror^{TOP}
- > PECVD Mirror_{BOT}
- > PECVD HT

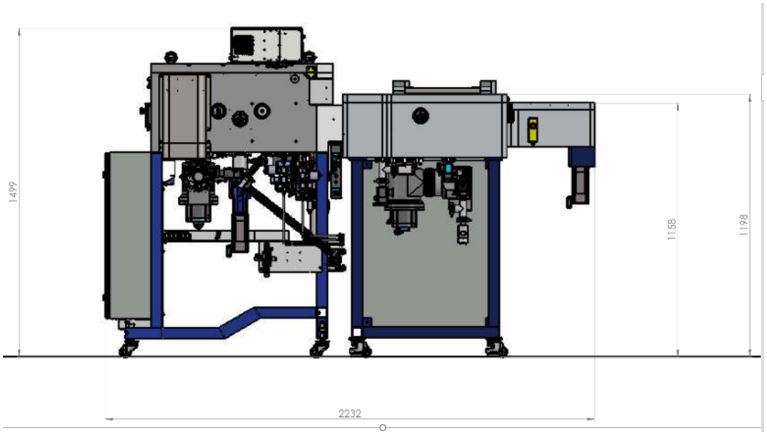


Fully compatible with classic OCTOPUS II carrier plates :

- > Area : 450x350 mm²
- > Up to 4x6" c-Si wafers
- > Up to 12x4" FZ c-Si wafers



- > Lifting system allowing easy manual loading of substrates
- > Fully automated (recipe-based) operation software
- > Includes all OCTOPUS II plasma control features



System key data

General	
Footprint L x W x H	2'232 x 800 x 1'500 mm ³
PECVD modules available	PECVD std PECVD HT PECVD Mirror ^{TOP} PECVD Mirror _{BOT}
Gas box architecture	Customizable gas box architecture including SiH ₄ , H ₂ , PH ₃ /H ₂ , TMB/H ₂ , B ₂ H ₆ /H ₂ , GeH ₄ /H ₂ , CH ₄ , N ₂ O, NH ₃ , NF ₃ , N ₂ , Ar, etc
Carrier plate size	450 x 350 mm ²
No. substrates per carrier plate	4x 6" c-Si wafers (M0, M2 or M4) 12x 4" c-Si wafers
Max substrate weight	2.5kg (including carrier plate)
Carrier plate nature	Spec. Aluminium (PECVD std, PECVD Mirror ^{TOP} , PECVD Mirror _{BOT}) Treated carbon fiber (PECVD HT)
Process	
Deposition side	TOP-side (PECVD std, PECVD HT, PECVD Mirror ^{TOP} ,) BOTTOM-side (PECVD Mirror _{BOT})
PECVD deposition mode	RF - 13.56 MHz, VHF on demand
Power density	0.01 to 0.5 W/cm ²
Process pressure	Typ. 0.5 to 10 mbar (up to 20 mbar on demand)
Base pressure	Loading module: < 1 · 10 ⁻⁵ mbar Process module: < 5 · 10 ⁻⁶ mbar
Thickness uniformity	<5% across entire carrier plate; < 3% run-to-run
Max Temperature	Up to 280°C (PECVD std, PECVD Mirror ^{TOP} , PECVD Mirror _{BOT}) Up to 400°C (PECVD HT)
Chamber cleaning	In-situ NF ₃ cleaning